

Features

- High isolation 5000 VRMS
- Patented coplanar structure DMC-Isolator®
- DC input with Darlington output
- Operating Temperature range 55 °C to 110 °C
- External creepage distance ≥ 7.4mm
- Distance Through Isolation ≥ 0.4mm
- Clearance Distance ≥ 7.5mm (S/SL Type)
- Clearance Distance ≥ 8.0mm (M/SLM Type)
- RoHS and REACH Compliance
- Halogen Free Compliance (Optional)
- MSL class 1
- Regulatory Approvals
 - ✓ UL UL1577 (E364000)
 - ✓ VDE EN60747-5-5(VDE0884-5)
 - ✓ CQC GB4943.1, GB8898 (14001104781)
 - ✓ IEC62368 (FI/41119)

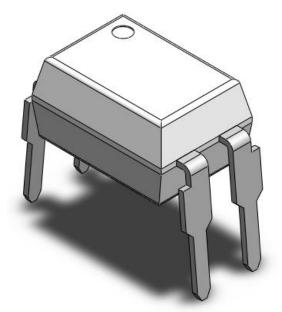
Description

The CT815 series consists of a photodarlington transistor optically coupled to an Infrared-emitting diode in a 4-lead DIP DMC-Isolator® package with different lead forming options.

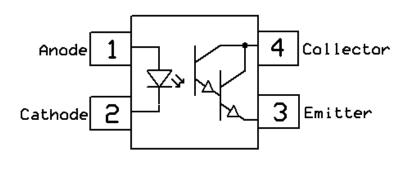
Applications

- Power supply regulators
- Digital logic outputs
- Microprocessor inputs

Package Outline



Schematic



Note: Different lead forming options available. See package dimension.



Absolute Maximum Ratings $T_A = 25^{\circ}C$, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes				
Viso	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V _{RMS}					
T _{OPR}	Operating temperature	-55 ~ +110	°C					
T _{STG}	Storage temperature	-55 ~ +150	°C					
T _{SOL}	Soldering temperature (For 10 seconds)	260	°C					
Ртот	Total power dissipation	200	mW					
Emitter	Emitter							
I _F	Forward current	60	mA					
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	А					
V _R	Reverse voltage	6	V					
P _D	Power dissipation	100	mW					
Detector	Detector							
Pc	Power dissipation	150	mW					
B _{VCEO}	Collector-Emitter Breakdown Voltage	40	V					
Bveco	Emitter-Collector Breakdown Voltage	7	V					
Ic	Collector Current	80	mA					

Electrical Characteristics $T_A = 25$ °C, unless otherwise specified

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =10mA	-	1.24	1.4	V	
I _R	Reverse Current	V _R = 6V	-	-	5	μΑ	
Cin	Input Capacitance	f= 1MHz	-	30	250	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B _{VCEO}	Collector-Emitter Breakdown	Ic= 100μA	40	-	-	V	
Bveco	Emitter-Collector Breakdown	I _E = 100μA	7	-	-	V	
ICEO	Collector-Emitter Dark Current	V _{CE} = 10V, I _F =0mA	-	-	1	μΑ	

Transfer Characteristics

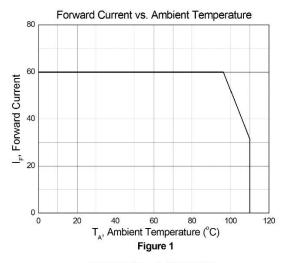
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
CTR	Current Transfer Ratio	I _F = 1mA, V _{CE} = 2V	600	ı	7500	%	
VCE(SAT)	Collector-Emitter Saturation Voltage	I _F = 20mA, I _C = 5mA	1	0.8	1	٧	
Rıo	Isolation Resistance	Vio= 500VDC	5x10 ¹⁰	-	-	Ω	
C _{IO}	Isolation Capacitance	f= 1MHz	-	0.25	1	pF	

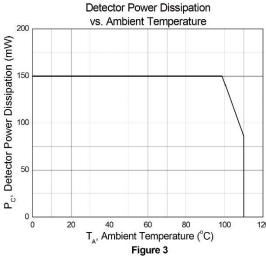
Switching Characteristics

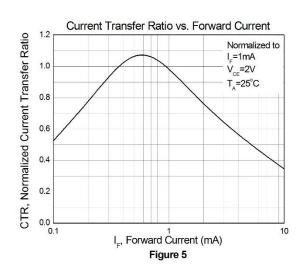
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
t _r	Rise Time	I _C = 10mA, V _{CE} = 2V,		-	300	0	
t _f	Fall Time	R _L = 100Ω	-	-	250	μS	

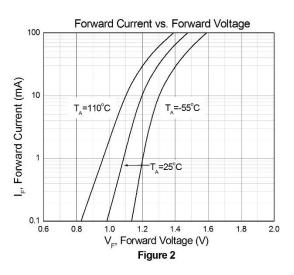


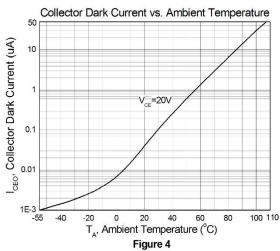
Typical Characteristic Curves $T_A = 25$ °C, unless otherwise specified

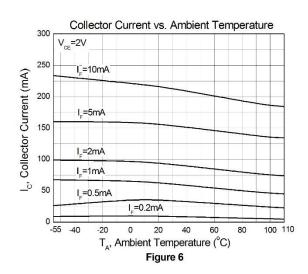






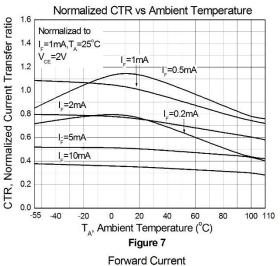


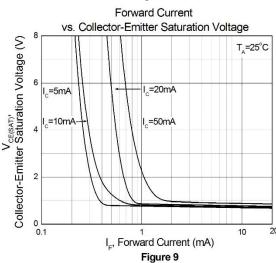


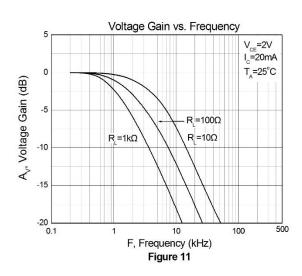


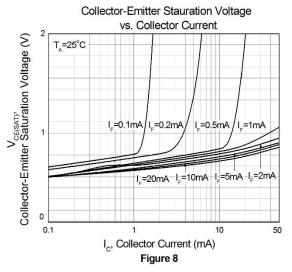


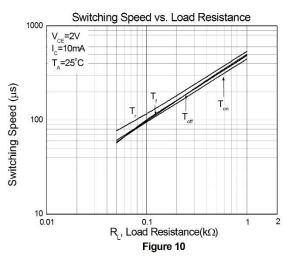
Typical Characteristic Curves $\tau_A = 25$ °C, unless otherwise specified (Continued)

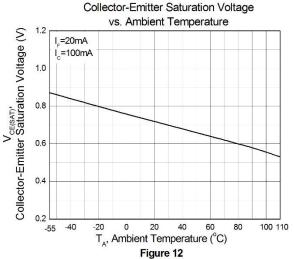














Test Circuit

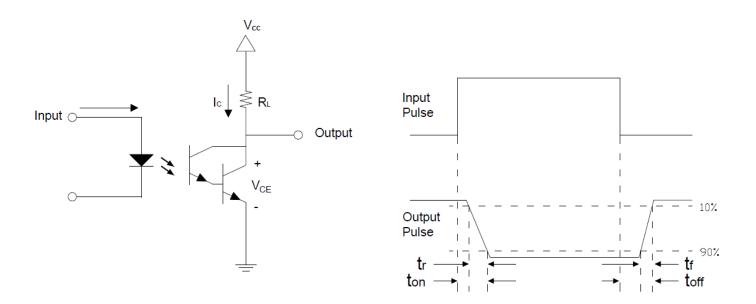
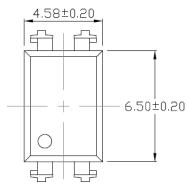


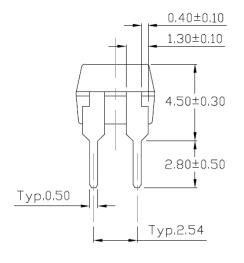
Figure 13: Switching Time Test Circuits

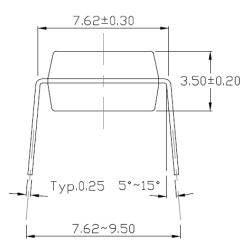


Package Dimension Dimensions in mm unless otherwise stated

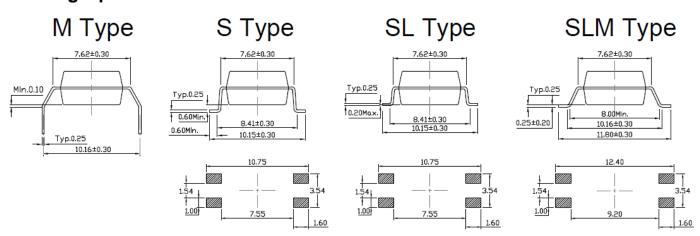
Standard DIP - Through Hole







Forming Option





Marking Information



Note:

CT : Denotes "CT Micro"

815 : Part Number

V : VDE Safety Mark Option (Blank or V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code

Ordering Information

CT815(Y)(Z)-G

CT = Denotes "CT Micro"

815 = Part Number

Y = Lead Form Option (S, SL, M, SLM or Blank)

Z = Tape and Reel Option (Blank, T1 or T2)

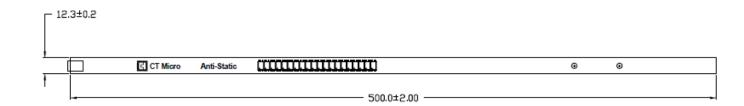
G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

Option	Description	Quantity
None	Standard 4 Pin DIP	100 Units/Tube
M	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	S(T2) Surface Mount Lead Forming – With Option 2 Taping	
SL(T1)	SL(T1) Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SLM(T1)	SLM(T1) Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	
SLM(T2) Surface Mount (Gullwing) Lead Forming – With Option 2 Taping		1500 Units/Reel

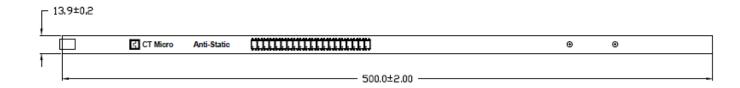


Carrier Specifications Dimensions in mm unless otherwise stated

Tube Option Standard DIP



Tube Option M Type

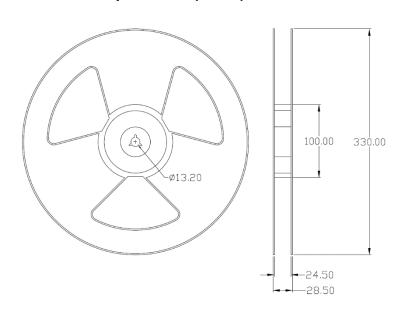


Reel Dimension All dimensions are in mm, unless otherwise stated

Option S(T1/T2) & SL(T1/T2)

100.00 330.00 Ø13.20 -16.50 -20.50

Option SLM(T1/T2)

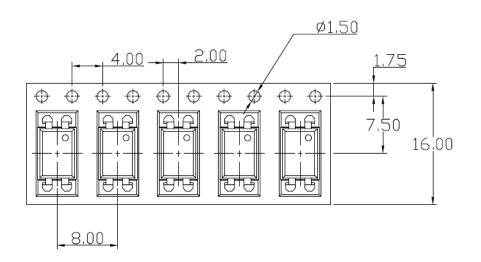


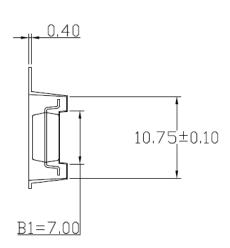


Carrier Tape Specifications Dimensions in mm unless otherwise stated

Option S(T1) & SL(T1)

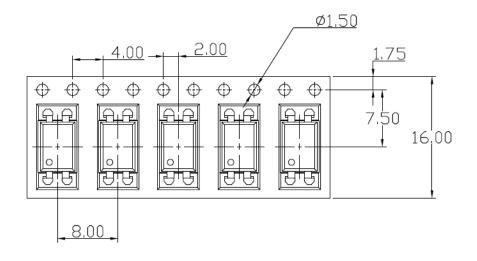
Input Direction

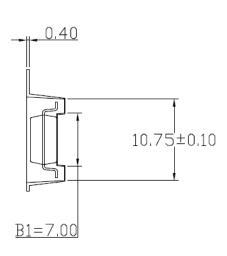




Option S(T2) & SL(T2)

Input Direction



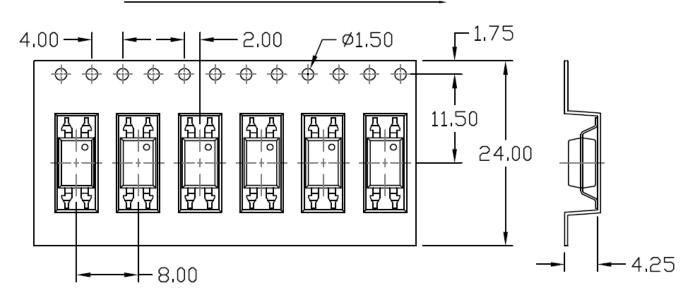






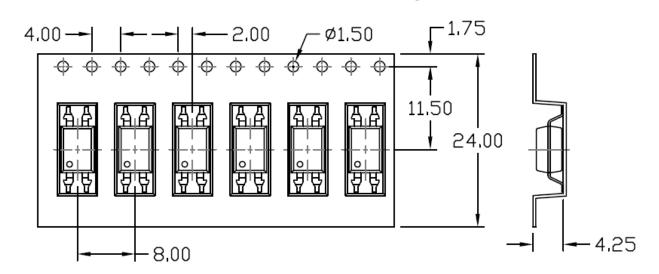
Option SLM(T1)

Input Direction



Option SLM(T2)

Input Direction





Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

Wave soldering (Follow the JEDEC standard JESD22-A111)

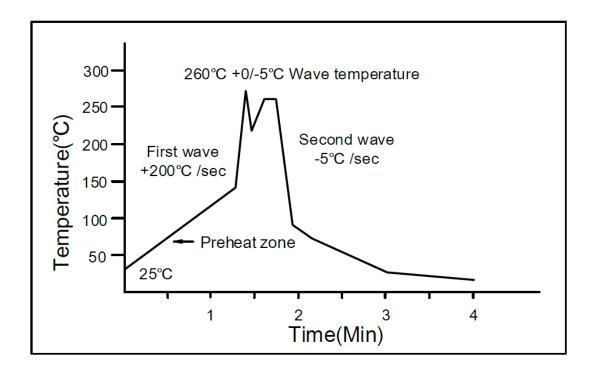
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature: 25 to 140°C.

Preheat time: 30 to 80 sec.



Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

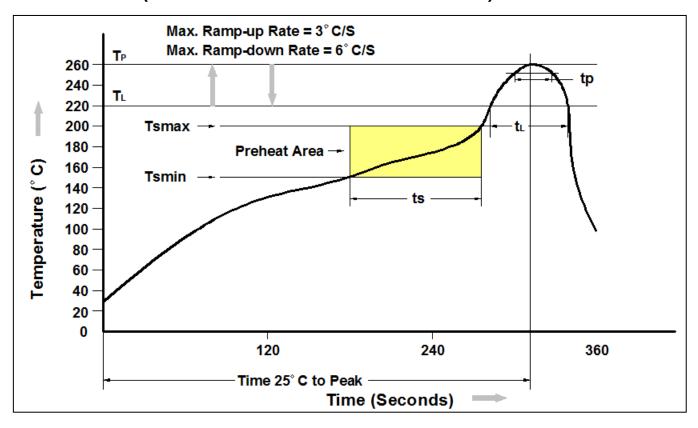
Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: 350±10°C

Time: 5 sec max.



Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t⊳)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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